

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1542-42** is a Common Base Device Designed for, IFF and DME Pulse Applications.

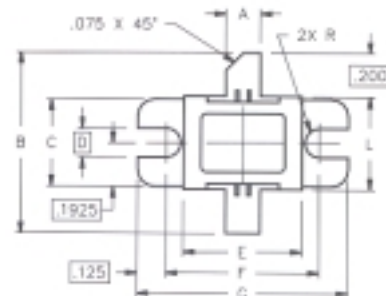
FEATURES INCLUDE:

- Gold Metalization
- Input/Output Matching
- Hermetically Sealed

MAXIMUM RATINGS

I_C	45 A
V_{CC}	55 V
P_{DISS}	1670 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.06 °C/W

PACKAGE STYLE .400 X 500 2L FLG



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.145/3.68	.155/3.93	I	.060/1.40	.065/1.65
B	.750/19.05		J	.115/2.92	.130/3.43
C	.380/9.65	.390/9.91	K		.230/5.64
D		.130/3.30	L	.395/10.03	.410/10.41
E	.495/12.57	.505/12.83			
F	.640/16.26	.655/16.64			
G	.880/22.61	.910/23.11			
H	.062/0.06	.066/0.15			

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 25 mA	65			V
BV_{CER}	I _C = 25 mA R _{BE} = 10 Ω	65			V
BV_{EBO}	I _E = 10 mA	3.5			V
I_{CES}	V _{CE} = 50 V			60	mA
h_{FE}	V _{CE} = 5.0 V I _C = 2.0 A	10		250	---
P_G	V _{CC} = 50 V P _{IN} = 150 W f = 1090 MHz PULSE	6.0	6.6		dB
η_C	WIDTH = 10 μS DUTY CYCLE = 1.0%	35	40		%
P_{OUT}		600	680		W